Maximum Ratings N-CHANNEL – Q_1 (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±6	V
Drain Current (Note 6)	T_A = +25°C T_A = +85°C	I_D	1.34 0.97	A

Maximum Ratings P-CHANNEL – Q_2 (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±6	V
Drain Current (Note 6)	T_A = +25°C T_A = +85°C	I_D	-1.14 -1.07	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	1.12	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	111	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Note: 6. For a device mounted on 25mm x 25mm FR-4 PCB board with a high coverage of single sided 1oz copper, in still air conditions with two active die.

Electrical Characteristics N-CHANNEL – Q_1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— — —	0.3 0.4 0.5	0.4 0.5 0.7	Ω	V_{GS} = 4.5V, I_D = 600mA V_{GS} = 2.5V, I_D = 500mA V_{GS} = 1.8V, I_D = 350mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	1.4	—	S	V_{DS} = 10V, I_D = 400mA
Diode Forward Voltage (Note 7)	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 150mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	60.67	—	pF	V_{DS} = 16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	9.68	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	5.37	—	pF	
Total Gate Charge	Q_g	—	736.6	—	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	93.6	—		
Gate-Drain Charge	Q_{gd}	—	116.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.1	—	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_G = 10Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	7.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.7	—		
Turn-Off Fall Time	t_F	—	12.3	—		

Electrical Characteristics P-CHANNEL – Q_2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.5 0.7 1.0	0.7 0.9 1.3	Ω	V_{GS} = -4.5V, I_D = -430mA V_{GS} = -2.5V, I_D = -300mA V_{GS} = -1.8V, I_D = -150mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	-0.9	—	S	V_{DS} = -10V, I_D = -250mA
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -150mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	59.76	—	pF	V_{DS} = -16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	12.07	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	6.36	—	pF	
Total Gate Charge	Q_g	—	622.4	—	pC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -250mA
Gate-Source Charge	Q_{gs}	—	100.3	—		
Gate-Drain Charge	Q_{gd}	—	132.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.1	—	ns	V_{DD} = -10V, V_{GS} = -4.5V, R_L = 47Ω, R_G = 10Ω, I_D = -200mA
Turn-On Rise Time	t_R	—	8.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	28.4	—		
Turn-Off Fall Time	t_F	—	20.7	—		

Note: 7. Short duration pulse test used to minimize self-heating effect.

N-CHANNEL – Q_1

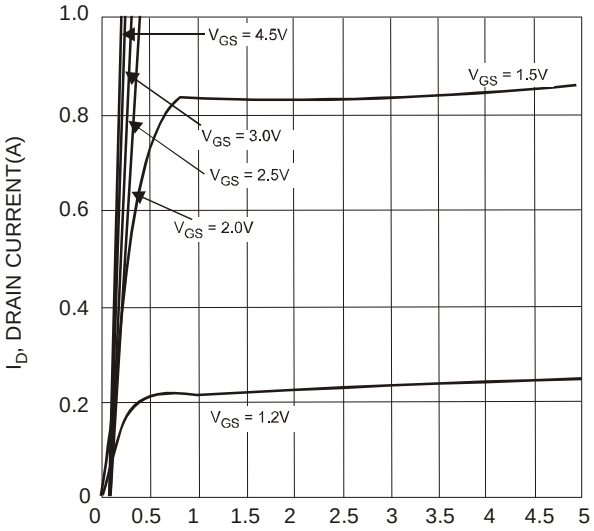


Fig.1 Typical Output Characteristics

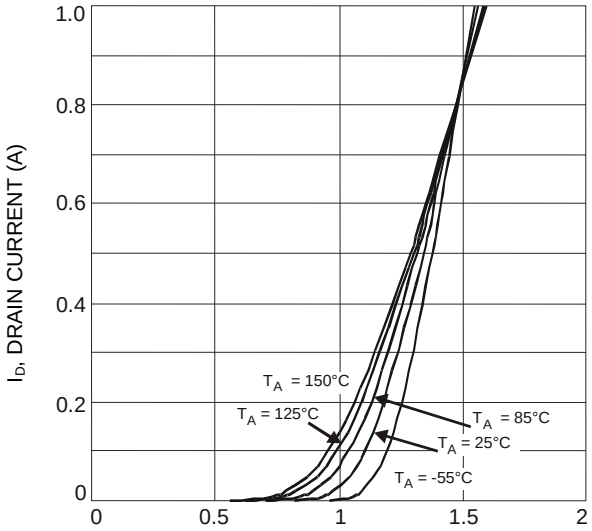


Fig. 2 Typical Transfer Characteristic

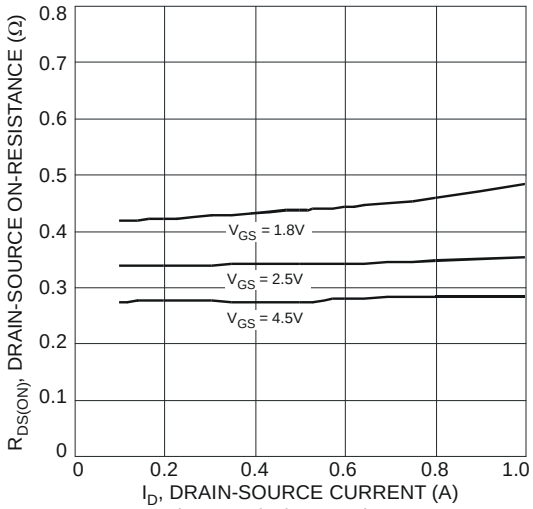


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

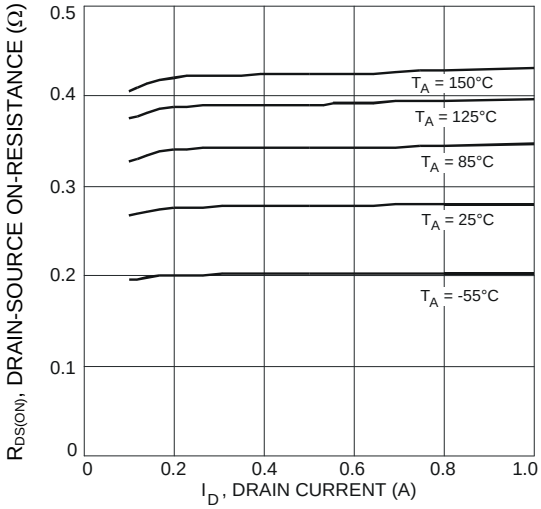


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

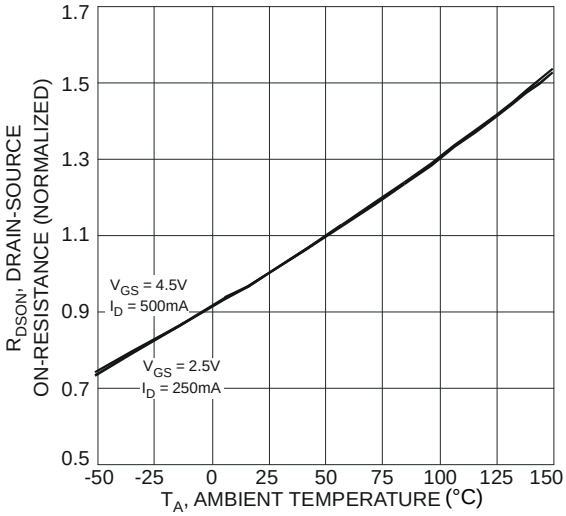


Fig. 5 On-Resistance Variation with Temperature

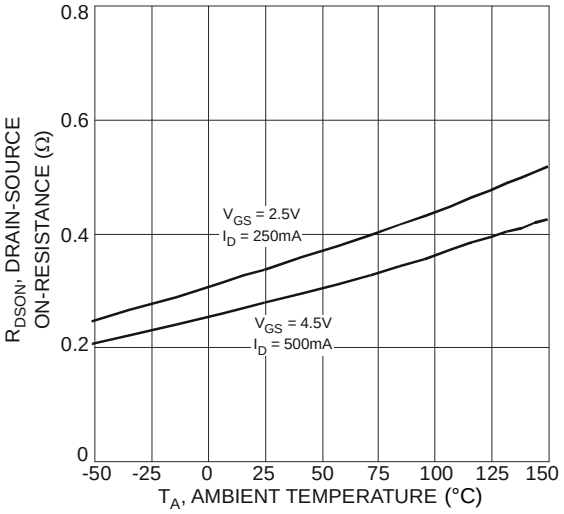


Fig. 6 On-Resistance Variation with Temperature

N-CHANNEL – Q_1 (Cont.)

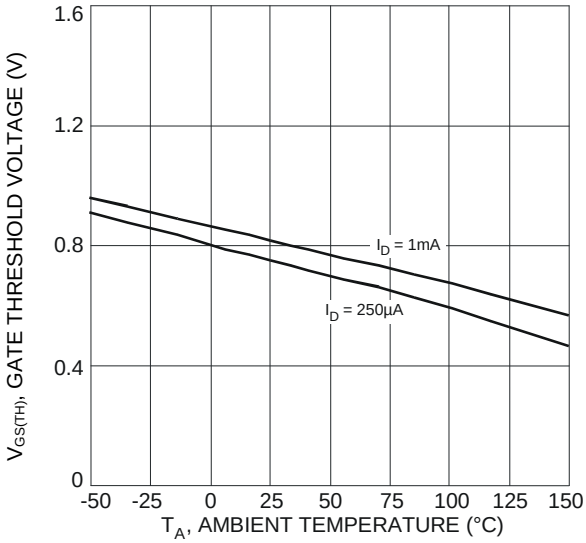


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

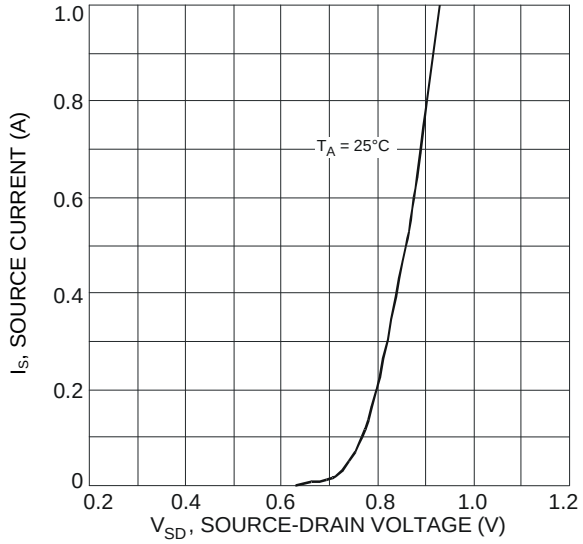


Fig. 8 Diode Forward Voltage vs. Current

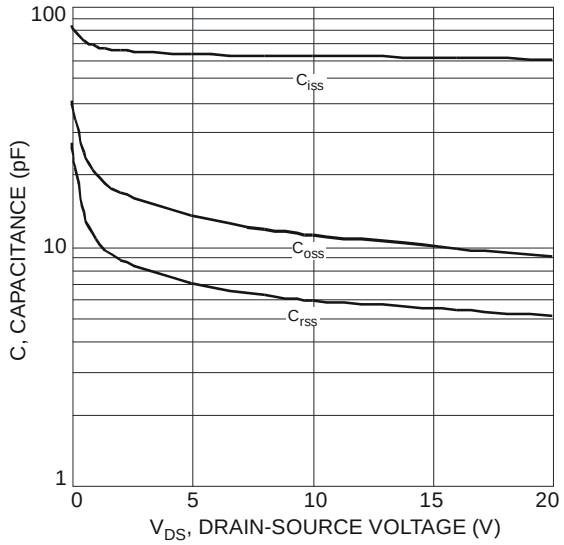


Fig. 9 Typical Total Capacitance

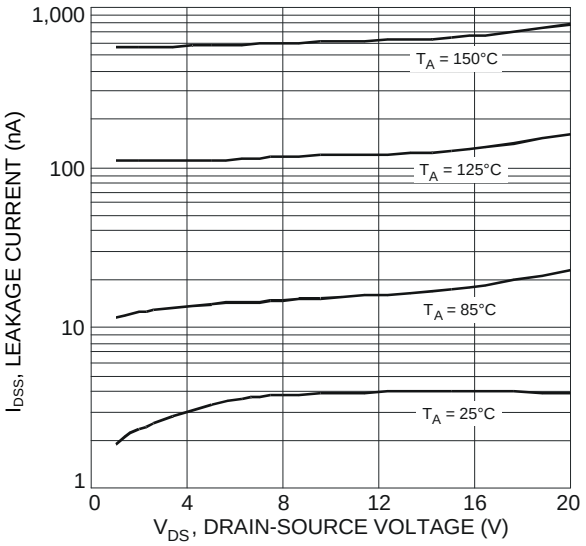


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

P-CHANNEL – Q_2

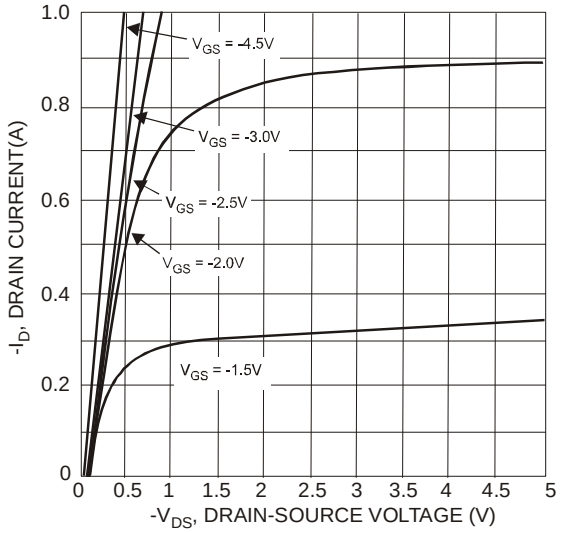


Fig.11 Typical Output Characteristics

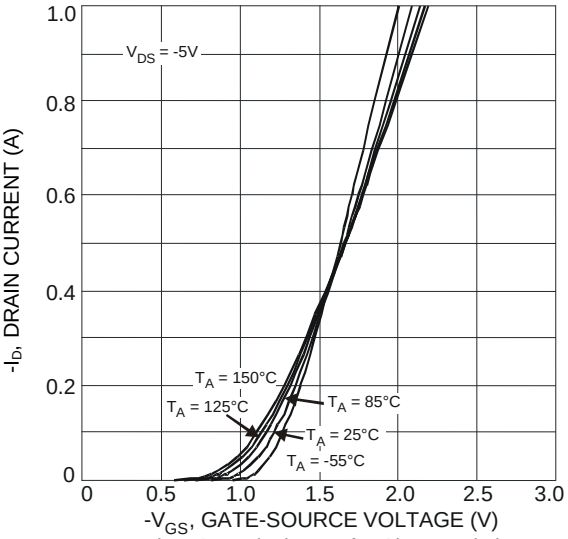


Fig. 12 Typical Transfer Characteristic

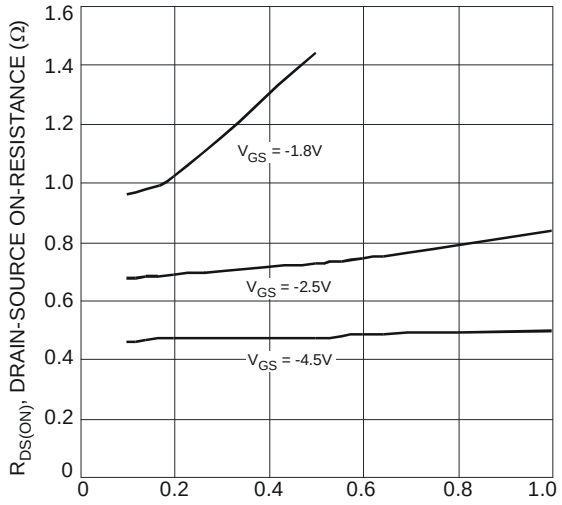


Fig. 13 Typical On-Resistance
vs. Drain Current and Gate Voltage

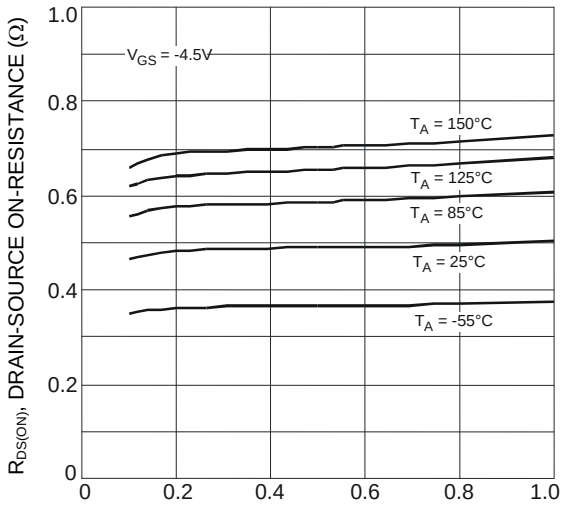


Fig. 14 Typical On-Resistance
vs. Drain Current and Temperature

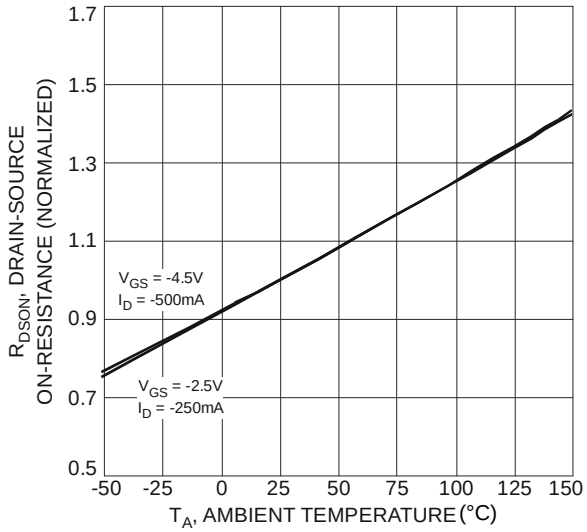


Fig. 15 On-Resistance Variation with Temperature

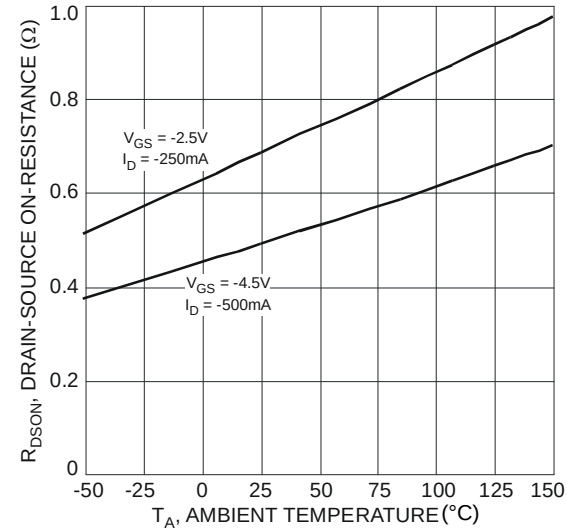


Fig. 16 On-Resistance Variation with Temperature

P-CHANNEL – Q_2 (Cont.)

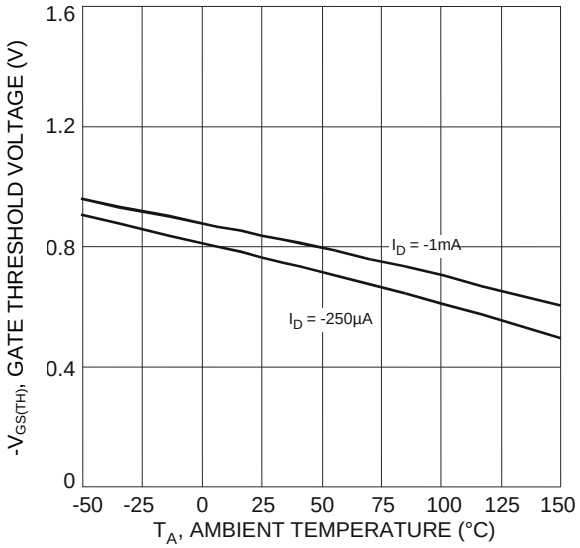


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

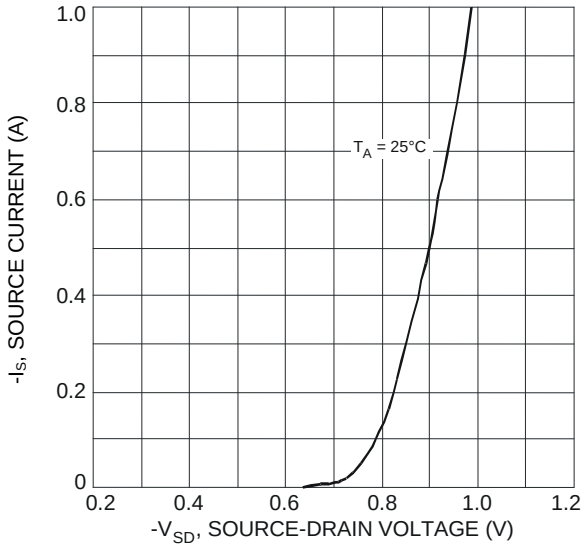


Fig. 18 Diode Forward Voltage vs. Current

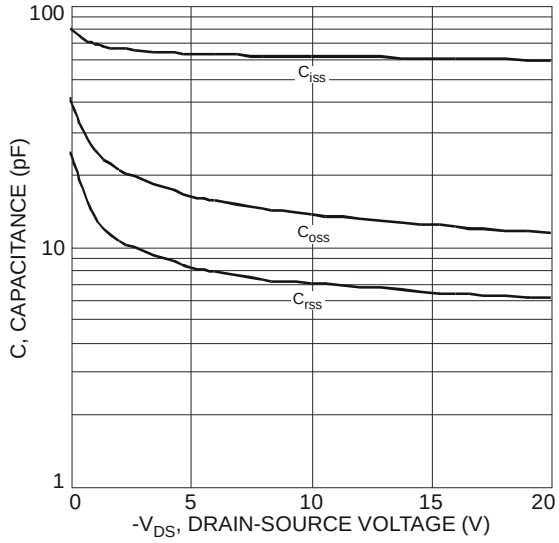


Fig. 19 Typical Total Capacitance

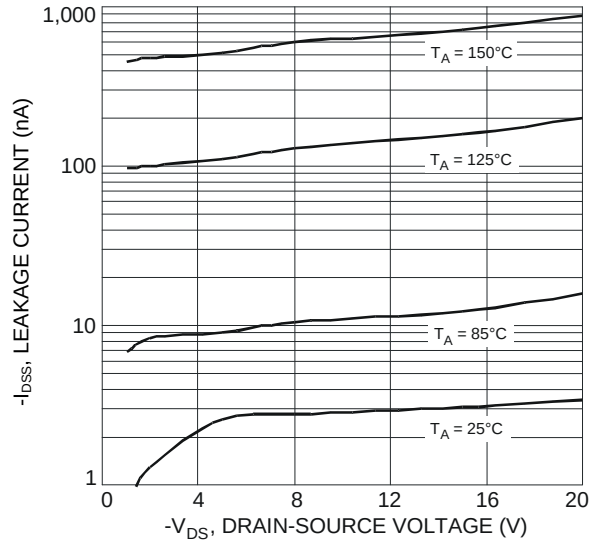
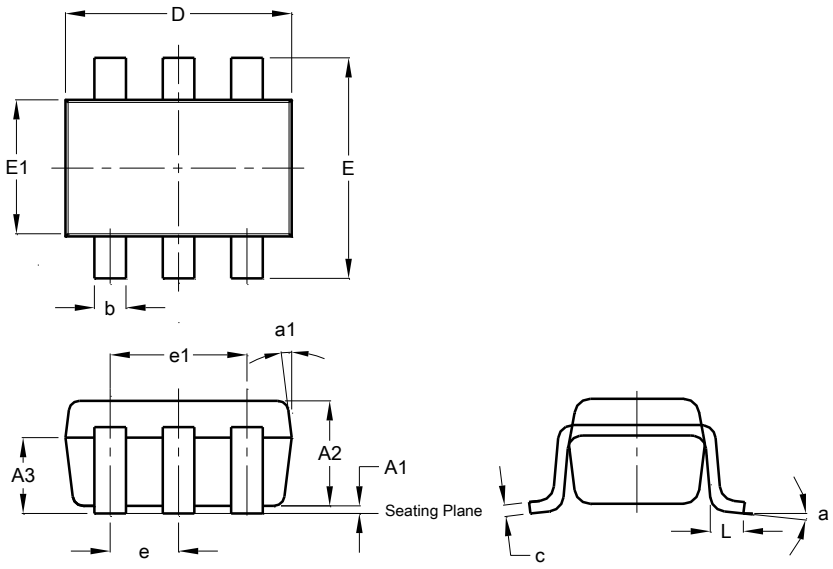


Fig. 20 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

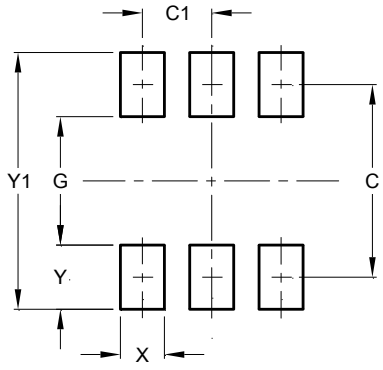


SOT26			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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